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Local metal-insulator transitions in V₂O₃ thin films studied by ⁵⁷Fe emission Mössbauer spectroscopy

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Metal to Insulator-to-transitions (MIT) driven by electronic interactions in strongly correlated materials are among the most remarkable phenomena in condensed matter physics. It has been found important applications in the next-generation so-called “beyond silicon” electronics and neuromorphic devices. Vanadium sesquioxide V₂O₃ is a prototypical Mott insulator, which undergoes the MIT between an antiferromagnetic insulator (AFI) and a paramagnetic metal (PM) or a paramagnetic insulator (PI) by varying the temperature, pressure, doping of material or photoexcitation. However, the origin of MIT in V₂O₃ is still an on-going topic of active study owing to a complex interplay of multiple factors, such as the crystal-field splitting, electron-lattice interaction and orbital degeneracy, in the Mott transition. Particularly, in the thin film V₂O₃, the magnitude and temperature of the transition can be greatly affected by the local structural defects, material stoichiometry and film stress. Here we present the ⁵⁷Fe emission Mössbauer spectroscopy study of the local MIT transition in the V₂O₃ thin films, which were grown with different crystalline and structural properties. The results show that...

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